

W27E010



128K × 8 ELECTRICALLY ERASABLE EPROM

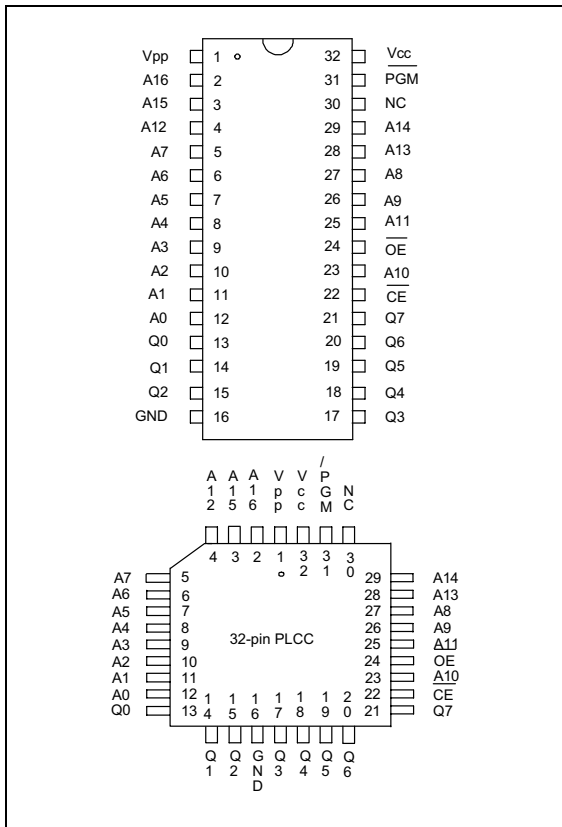
GENERAL DESCRIPTION

The W27E010 is a high speed, low power Electrically Erasable and Programmable Read Only Memory organized as 131072 × 8 bits that operates on a single 5 volt power supply. The W27E010 provides an electrical chip erase function.

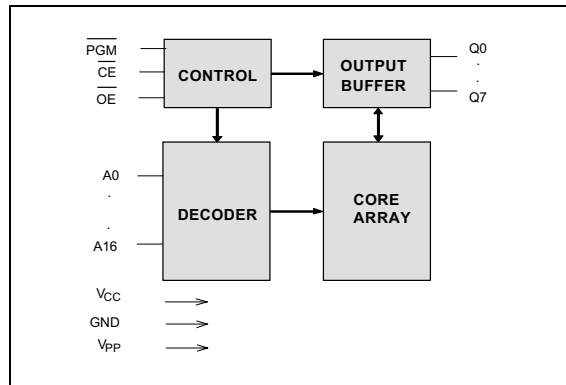
FEATURES

- High speed access time: 45/55/70/90/120 nS (max.)
- Read operating current: 30 mA (typ.)
- Erase/Programming operating current: 1 mA (typ.)
- Standby current: 5 μA (typ.)
- Single 5V power supply
- +14V erase/+12V programming voltage
- Fully static operation
- All inputs and outputs directly TTL/CMOS compatible
- Three-state outputs
- Available packages: 32-pin 600 mil DIP, 450 mil SOP and PLCC

PIN CONFIGURATIONS



BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0–A16	Address Inputs
Q0–Q7	Data Inputs/Outputs
\overline{CE}	Chip Enable
\overline{OE}	Output Enable
PGM	Program Enable
VPP	Program/Erase Supply Voltage
VCC	Power Supply
GND	Ground
NC	No Connection

FUNCTIONAL DESCRIPTION